

OptiMOS™ 3 Power-Transistor
Features

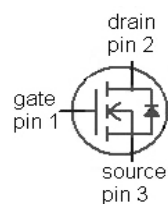
- MOSFET for ORing and Uninterruptible Power Supply
- Qualified according to JEDEC¹⁾ for target applications
- N-channel
- Normal level
- Ultra-low on-resistance $R_{DS(on)}$
- 100% Avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	40	V
$R_{DS(on),max}$	2.3	m Ω
I_D	90	A



Type	IPB023N04N G	IPP023N04N G
Package	PG-TO263-3	PG-TO220-3
Marking	023N04N	023N04N


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$	90	A
		$V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$	90	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	400	
Avalanche current, single pulse ³⁾	I_{AS}	$T_C=25\text{ °C}$	90	
Avalanche energy, single pulse	E_{AS}	$I_D=90\text{ A}$, $R_{GS}=25\text{ }\Omega$	150	mJ
Gate source voltage	V_{GS}		± 20	V

¹⁾ J-STD20 and JESD22

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	167	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	0.9	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ⁴⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$	40	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=95\text{ }\mu\text{A}$	2	-	4	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=40\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{\text{DS}}=40\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance ⁵⁾	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=90\text{ A}$	-	1.9	2.3	m Ω
Gate resistance	R_{G}		-	1.9	-	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}, I_{\text{D}}=90\text{ A}$	75	150	-	S

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

⁵⁾ Measured from drain tab to source pin

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V},$ $f=1\text{ MHz}$	-	7300	10000	pF
Output capacitance	C_{oss}		-	2000	2700	
Reverse transfer capacitance	C_{rss}		-	77	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{ V}, V_{GS}=10\text{ V},$ $I_D=30\text{ A}, R_G=1.6\ \Omega$	-	27	-	ns
Rise time	t_r		-	6.6	-	
Turn-off delay time	$t_{d(off)}$		-	40	-	
Fall time	t_f		-	7.8	-	

Gate Charge Characteristics⁶⁾

Gate to source charge	Q_{gs}	$V_{DD}=20\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	35	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	22	-	
Gate to drain charge	Q_{gd}		-	11	-	
Switching charge	Q_{sw}		-	24	-	
Gate charge total	Q_g		-	90	120	
Gate plateau voltage	$V_{plateau}$		-	4.8	-	
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V},$ $V_{GS}=0\text{ to }10\text{ V}$	-	85	-	nC
Output charge	Q_{oss}	$V_{DD}=20\text{ V}, V_{GS}=0\text{ V}$	-	73	-	

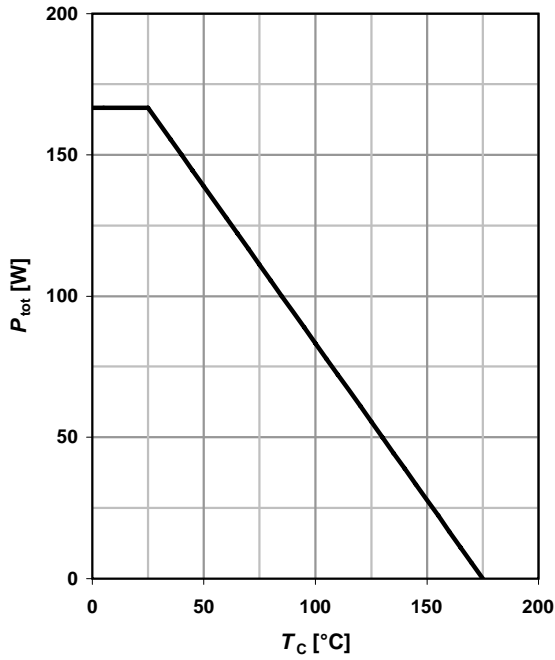
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	90	A
Diode pulse current	$I_{S,pulse}$		-	-	400	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=90\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.93	1.2	V
Reverse recovery charge	Q_{rr}	$V_R=20\text{ V}, I_F=I_S,$ $di_F/dt=400\text{ A}/\mu\text{s}$	-	80	-	nC

⁶⁾ See figure 16 for gate charge parameter definition

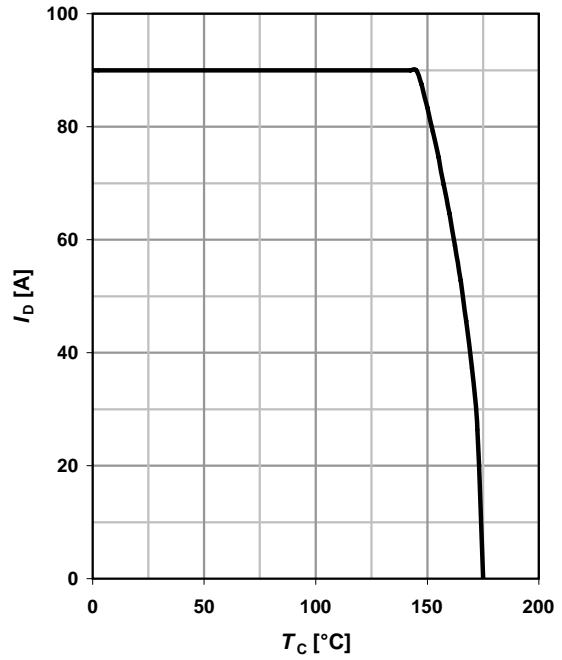
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

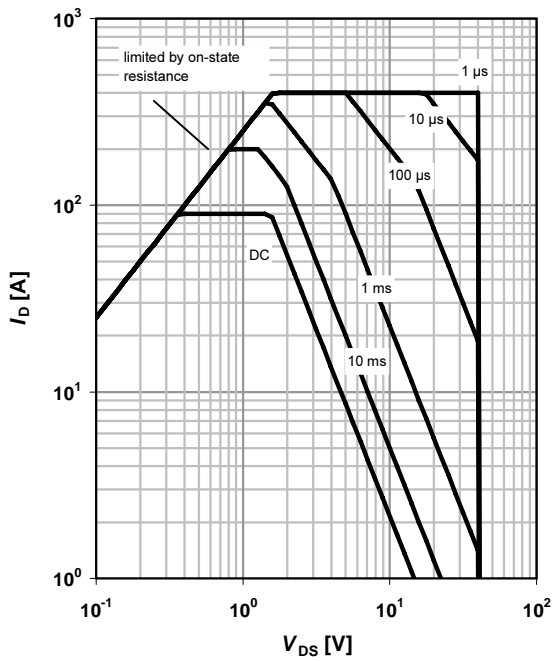
$I_D=f(T_C); V_{GS} \geq 10 V$



3 Safe operating area

$I_D=f(V_{DS}); T_C=25^\circ C; D=0$

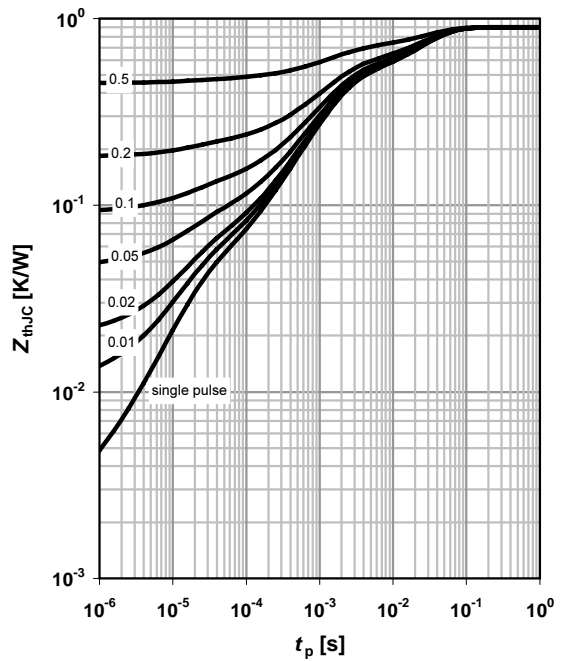
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

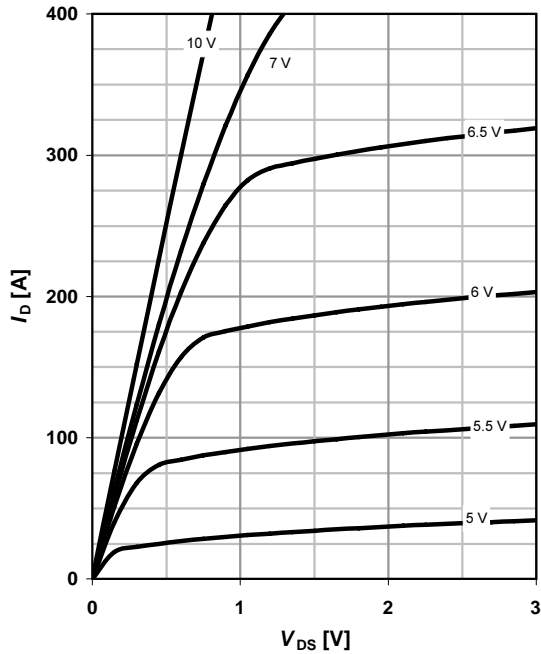
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_J = 25\text{ °C}$

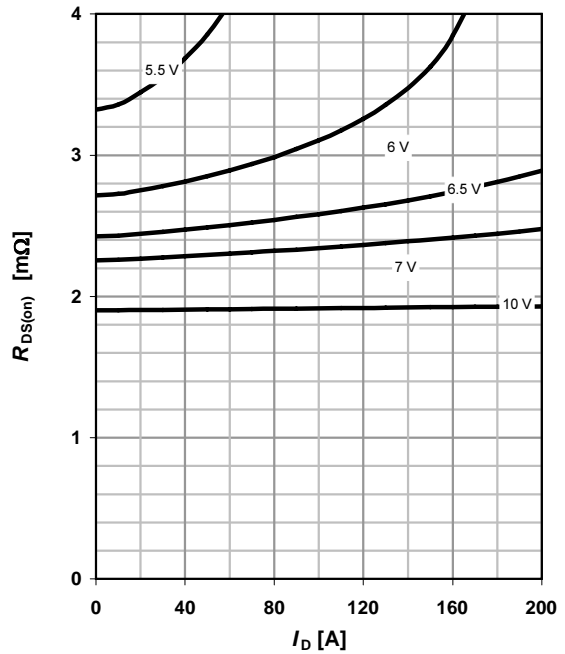
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_J = 25\text{ °C}$

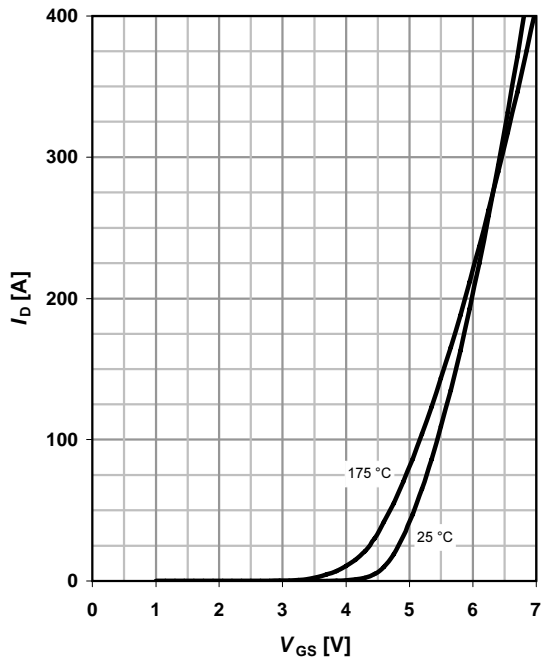
parameter: V_{GS}



7 Typ. transfer characteristics

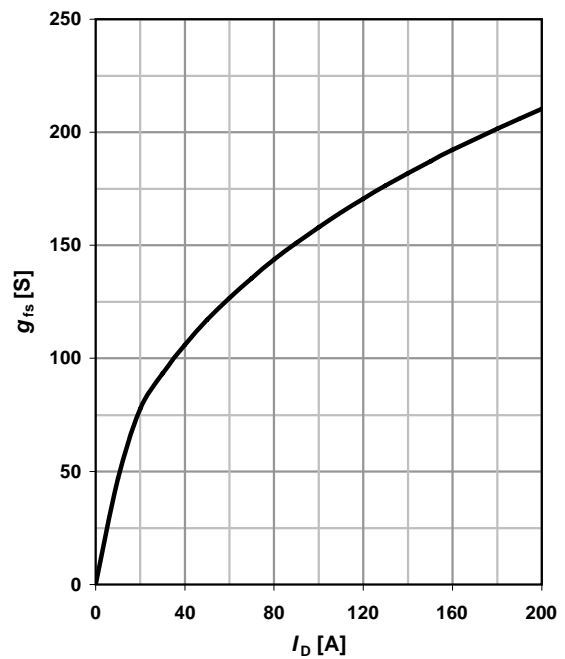
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_J



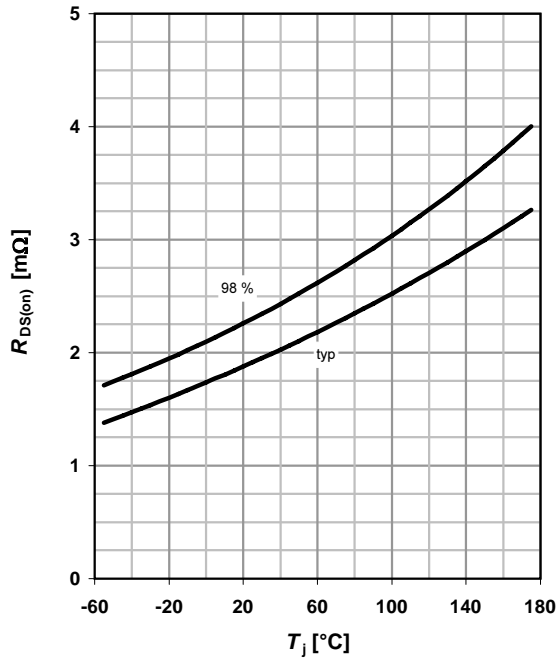
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_J = 25\text{ °C}$



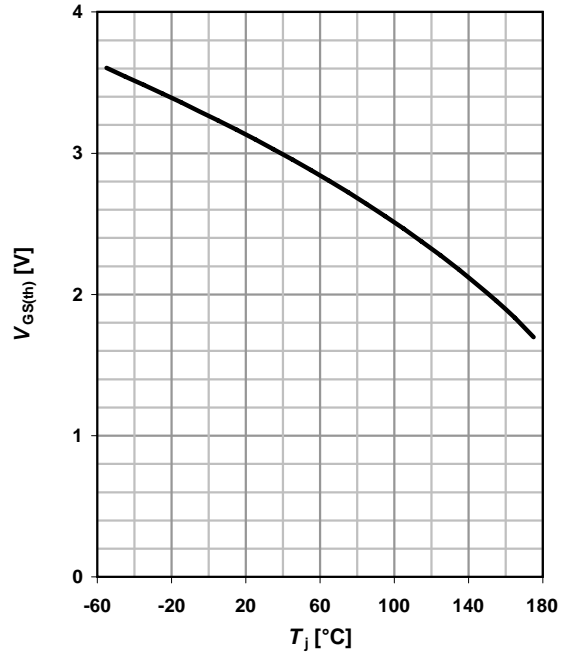
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = 90 \text{ A}; V_{GS} = 10 \text{ V}$



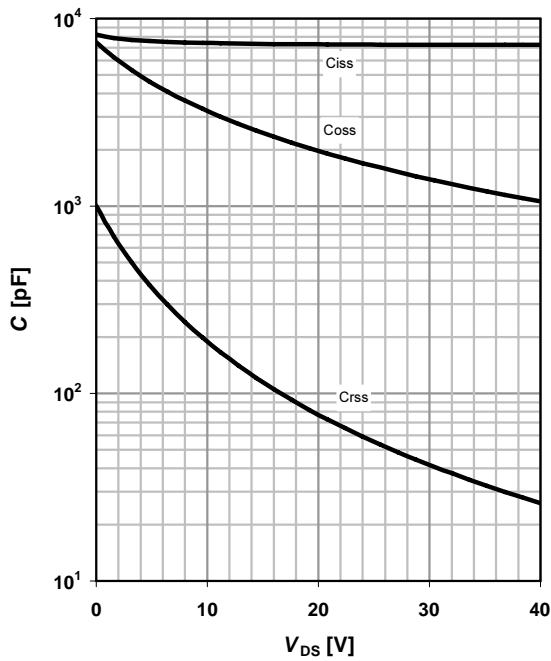
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu\text{A}$



11 Typ. capacitances

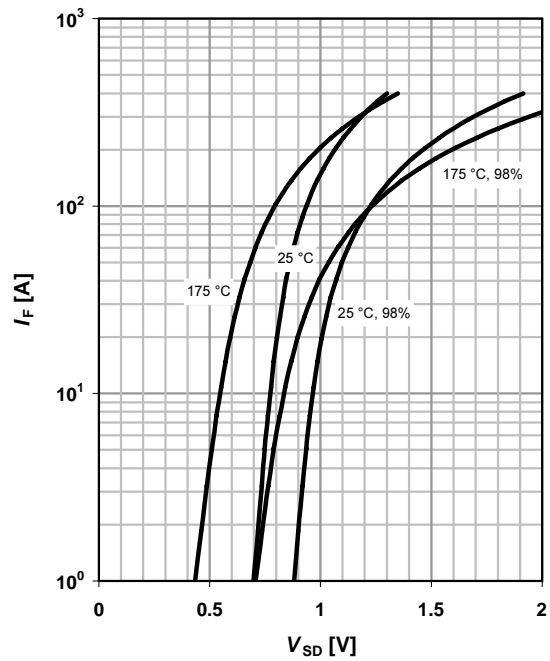
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

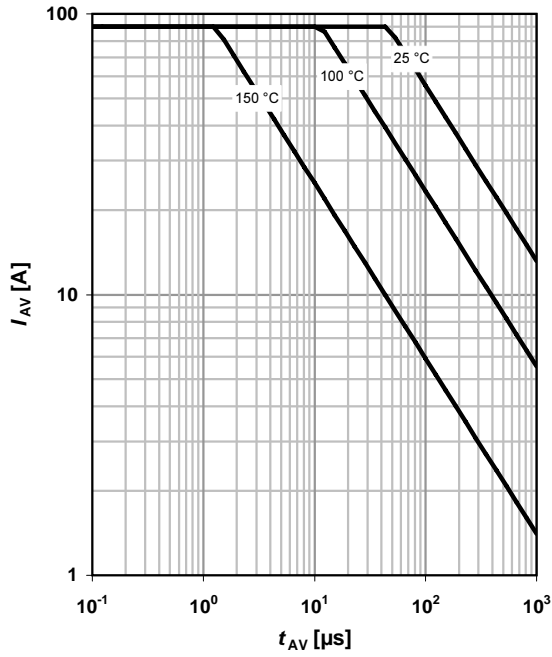
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

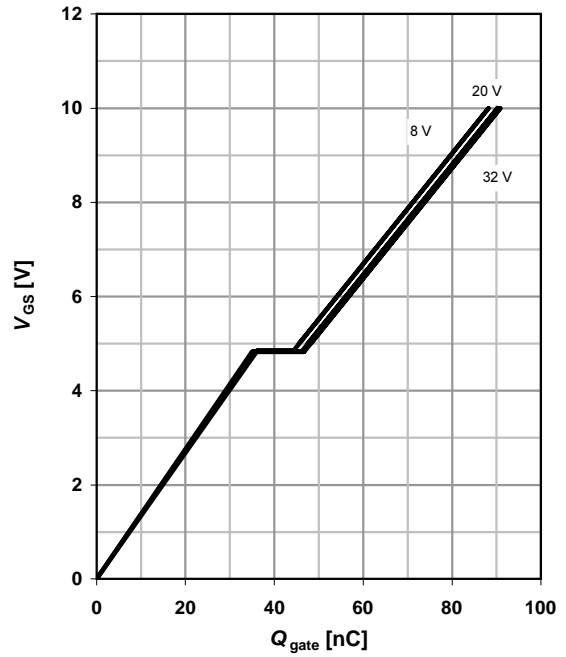
parameter: $T_{j(start)}$



14 Typ. gate charge

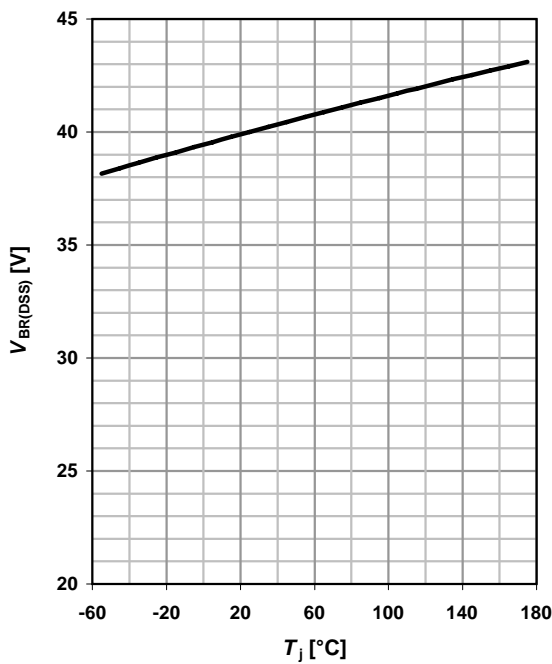
$V_{GS}=f(Q_{gate}); I_D=30 \text{ A pulsed}$

parameter: V_{DD}

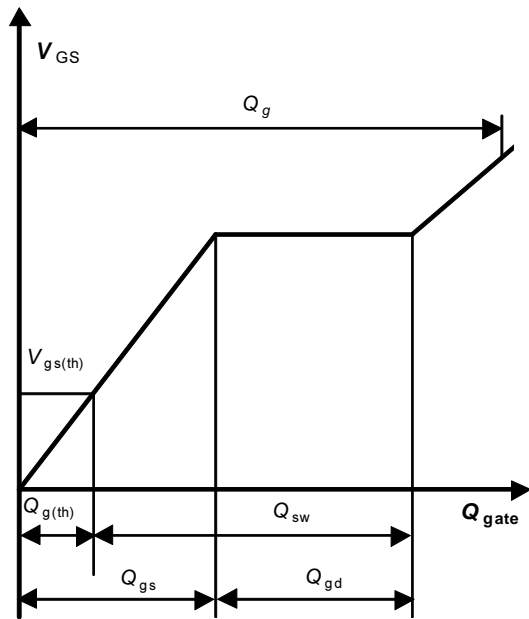


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms





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